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IN THE CLAIMS

1. (Original) An apparatus comprising:
- (a) a deposition chamber, wherein the deposition chamber is divided into two or more deposition regions that are integrally connected to one another; and
 - (b) a wafer support disposed in the deposition chamber, wherein the wafer support is moveable between the two or more interconnected deposition regions.
2. (Original) The apparatus of claim 1 wherein a piston coupled to the wafer support moves the wafer support between the two or more interconnected deposition regions.
3. (Previously Amended) The apparatus of claim 1, further comprising a heater wherein the heater is adapted to control the temperature of the wafer support.
4. (Previously Amended) The apparatus of claim 1 wherein the wafer support is an electrostatic chuck.
5. (Original) The apparatus of claim 1, wherein each of the two or more deposition regions are integrally connected to another of the two or more deposition regions with an aperture.
6. (Original) The apparatus of claim 5 wherein the aperture is sealed to minimize the intermixing of deposition gases between the two or more deposition regions.
7. (Original) The apparatus of claim 1, further comprising a gas supply panel coupled to the deposition chamber.

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8. (Original) The apparatus of claim 7 wherein the gas supply panel includes one or more gas supply lines which couple the gas supply panel to the deposition chamber.

9. (Original) The apparatus of claim 1, further comprising a gas exhaust pump coupled to the deposition chamber.

10. (Original) A method of depositing a material layer on a substrate comprising:

CI (a) positioning a substrate on a wafer support in a deposition chamber comprising a first and second deposition region, wherein the first and second deposition regions are integrally connected to one another, and wherein the wafer support is movable between the first and second deposition regions;

(b) introducing a first deposition gas into the first deposition region and a second deposition gas into the second deposition region;

(c) moving the wafer support with the substrate thereon into the first deposition region wherein a first monolayer of the first deposition gas is chemisorbed onto the surface of the substrate;

(d) moving the wafer support with the substrate thereon into the second deposition region wherein a first monolayer of the second deposition gas is chemisorbed on the first monolayer of the first deposition gas; and

(e) repeating steps (c) and (d) until a material layer having a desired thickness is achieved.

11. (Original) A computer storage medium containing a software routine that when executed causes a general purpose computer to control a process chamber using a layer deposition method, comprising:

(a) positioning a substrate on a wafer support in a deposition chamber comprising a first and second deposition region, wherein the first and second deposition regions are integrally connected to one another, and wherein the wafer support is movable between the first and second deposition regions;

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(b) introducing a first deposition gas into the first deposition region and a second deposition gas into the second deposition region;

(c) moving the wafer support with the substrate thereon into the first deposition region wherein a first monolayer of the first deposition gas is chemisorbed onto the surface of the substrate;

(d) moving the wafer support with the substrate thereon into the second deposition region wherein a first monolayer of the second deposition gas is chemisorbed on the first monolayer of the first deposition gas; and

(e) repeating steps (c) and (d) until a material layer having a desired thickness is achieved.

12. (Previously Amended) The method of claim 11, wherein the step of moving the substrate support to the second deposition region further comprises:
changing the elevation of the substrate support.

13. (Previously Amended) The apparatus of claim 1, wherein the first and second deposition regions are vertically stacked.

14. (Previously Amended) The apparatus of claim 1, wherein the chamber further comprises:

a first orifice adapted to provide process gas to the first deposition region;
and

a second orifice adapted to provide process gas to the second deposition region.

15. (Previously Amended) The apparatus of claim 14, wherein the first orifice is disposed vertically above the second orifice.

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16. (Previously Amended) The method of claim 10, wherein the step of moving the substrate support to the second deposition region further comprises:
changing the elevation of the substrate support.

17. (Currently Amended) A method of depositing a material layer on a substrate comprising:

positioning a substrate on a wafer substrate support in a deposition chamber comprising a first deposition region and a second deposition region, wherein the first and second deposition regions are integrally connected to one another;

depositing a first monolayer on the wafer substrate disposed on the substrate support in the first deposition region;

moving the wafer positioned on the substrate support to the second deposition region; and

depositing a layer on the wafer substrate in the second deposition region;

18. (Currently Amended) The method of claim 17 further comprising:

depositing a second monolayer on the wafer substrate in the first deposition region.

19. (Previously Amended) The method of claim 17 further comprising:

introducing a first deposition gas to form the first monolayer in the first deposition region; and

introducing a second deposition gas to deposit the layer in the second deposition region.

20. (New) An apparatus for processing a substrate comprising:

a deposition chamber wherein the deposition chamber is divided into two or more deposition regions that are integrally connected to one another, at least one of said regions being adapted to support deposition of a monolayer upon a surface of a substrate; and

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a wafer support disposed in the deposition chamber, wherein the wafer support is moveable between two or more interconnected deposition regions.

21. (New) The apparatus of claim 20 in which at least one of said regions is sealed so as to minimize intermixing of deposition gases within two or more deposition regions.

22. (New) The apparatus of claim 20 in which said chamber further comprises an orifice for each of said deposition regions, each orifice adapted to provide process gas to a respective deposition region

23. (New) The apparatus of claim 22, in which each orifice is adapted to provide differing process gases.

24. (New) The apparatus of claim 22 in which at least one of said orifices is adapted to provide process gas and purge gas.

25. (New) The apparatus of claim 20 wherein one of said deposition regions is vertically stacked above another of said deposition regions.

26. (New) The apparatus of claim 20 wherein the deposition regions are positioned side by side.

27. (New) The apparatus of claim 20 in which said at least one deposition region is adapted to support deposition of a second monolayer

28. (New) The apparatus of claim 20 in which said at least one deposition region is adapted to support deposition via chemisorption.

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29. (New) An apparatus for processing a substrate, comprising:
a deposition chamber wherein the deposition chamber is divided into two or more deposition regions that are integrally interconnected to one another, at least one of said deposition regions being adapted to support deposition of a first monolayer upon a surface of a substrate and at least one of said deposition regions being optionally sealable from the other deposition regions; and
a wafer support disposed in the deposition chamber, wherein the wafer support is moveable between two or more interconnected deposition regions.
30. (New) The apparatus of 29 in which said at least one regions is adapted to support deposition of a second monolayer.
31. (New) The apparatus of claim 29 in which at least one of said regions is sealed so as to minimize intermixing of deposition gases within two or more deposition regions.
32. (New) The apparatus of claim 29 in which said chamber further comprises an orifice for each of said deposition regions, each orifice adapted to provide process gas to a respective deposition region
33. (New) The apparatus of claim 22, in which each orifice is adapted to provide differing process gases.
34. (New) The apparatus of claim 22 in which at least one of said orifices is adapted to provide process gas and purge gas.
35. (New) The apparatus of claim 29 wherein one of said deposition regions is vertically stacked above another of said deposition regions.

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36. (New) The apparatus of claim 29 wherein the deposition regions are positioned side by side.

37. (New) The apparatus of claim 29 in which said at least one deposition region is adapted to support deposition of a second monolayer

38. (New) The apparatus of claim 29 in which said at least one deposition region is adapted to support deposition via chemisorption.

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39. (New) The method of claim 19 further comprising:
flowing a purge gas into at least one of the integrally connected deposition regions between the introduction of the first and second deposition gases.

40. (New) The method of claim 19, wherein the step of moving the wafer positioned on the substrate support to the second deposition region further comprises:

moving the substrate support vertically.

41. (New) The method of claim 19, wherein the step of moving the wafer positioned on the substrate support to the second deposition region further comprises:

moving the substrate support horizontally.